

XC7SHU04

Inverter

Rev. 01 — 7 September 2009

Product data sheet

1. General description

The XC7SHU04 is a high-speed Si-gate CMOS device. It provides an inverting single stage function.

2. Features

- Symmetrical output impedance
- High noise immunity
- Low power dissipation
- Balanced propagation delays
- ESD protection:
 - ◆ HBM JESD22-A114E: exceeds 2000 V
 - ◆ MM JESD22-A115-A: exceeds 200 V
 - ◆ CDM JESD22-C101C: exceeds 1000 V
- Specified from -40 °C to +125 °C

3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
XC7SHU04GW	-40 °C to +125 °C	TSSOP5	plastic thin shrink small outline package; 5 leads; body width 1.25 mm	SOT353-1
XC7SHU04GV	-40 °C to +125 °C	SC-74A	plastic surface-mounted package; 5 leads	SOT753

4. Marking

Table 2. Marking codes

Type number	Marking ^[1]
XC7SHU04GW	fD
XC7SHU04GV	fU4

[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

5. Functional diagram

Fig 1. Logic symbol

Fig 2. IEC logic symbol

Fig 3. Logic diagram

6. Pinning information

6.1 Pinning

Fig 4. Pin configuration SOT353-1 and SOT753

6.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
n.c.	1	not connected
A	2	data input
GND	3	ground (0 V)
Y	4	data output
V _{CC}	5	supply voltage

7. Functional description

Table 4. Function table

H = HIGH voltage level; L = LOW voltage level

Input	Output
A	Y
L	H
H	L

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+7.0	V
I_{IK}	input clamping current	$V_I < -0.5\text{ V}$	-20	-	mA
V_I	input voltage		[1] -0.5	+7.0	V
I_{OK}	output clamping current	$V_O < -0.5\text{ V}$ or $V_O > V_{CC} + 0.5\text{ V}$	-	± 20	mA
I_O	output current	$-0.5\text{ V} < V_O < V_{CC} + 0.5\text{ V}$	-	± 25	mA
I_{CC}	supply current		-	75	mA
I_{GND}	ground current		-75	-	mA
T_{stg}	storage temperature		-65	+150	°C
P_{tot}	total power dissipation	$T_{amb} = -40\text{ °C}$ to $+125\text{ °C}$	[2] -	250	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For both TSSOP5 and SC-74A packages: above 87.5 °C the value of P_{tot} derates linearly with 4.0 mW/K.

9. Recommended operating conditions

Table 6. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{CC}	supply voltage		2.0	5.0	5.5	V
V_I	input voltage		0	-	5.5	V
V_O	output voltage		0	-	V_{CC}	V
T_{amb}	ambient temperature		-40	+25	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{CC} = 3.3\text{ V} \pm 0.3\text{ V}$	-	-	100	ns/V
		$V_{CC} = 5.0\text{ V} \pm 0.5\text{ V}$	-	-	20	ns/V

10. Static characteristics

Table 7. Static characteristics

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
V _{IH}	HIGH-level input voltage	V _{CC} = 2.0 V	1.7	-	-	1.7	-	1.7	-	V
		V _{CC} = 3.0 V	2.4	-	-	2.4	-	2.4	-	V
		V _{CC} = 5.5 V	4.4	-	-	4.4	-	4.4	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 2.0 V	-	-	0.3	-	0.3	-	0.3	V
		V _{CC} = 3.0 V	-	-	0.6	-	0.6	-	0.6	V
		V _{CC} = 5.5 V	-	-	1.1	-	1.1	-	1.1	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}								
		I _O = –50 µA; V _{CC} = 2.0 V	1.9	2.0	-	1.9	-	1.9	-	V
		I _O = –50 µA; V _{CC} = 3.0 V	2.9	3.0	-	2.9	-	2.9	-	V
		I _O = –50 µA; V _{CC} = 4.5 V	4.4	4.5	-	4.4	-	4.4	-	V
		I _O = –4.0 mA; V _{CC} = 3.0 V	2.58	-	-	2.48	-	2.40	-	V
V _{OL}	LOW-level output voltage	I _O = –8.0 mA; V _{CC} = 4.5 V	3.94	-	-	3.8	-	3.70	-	V
		V _I = V _{IH} or V _{IL}								
		I _O = 50 µA; V _{CC} = 2.0 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 50 µA; V _{CC} = 3.0 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 50 µA; V _{CC} = 4.5 V	-	0	0.1	-	0.1	-	0.1	V
I _I	input leakage current	I _O = 4.0 mA; V _{CC} = 3.0 V	-	-	0.36	-	0.44	-	0.55	V
		I _O = 8.0 mA; V _{CC} = 4.5 V	-	-	0.36	-	0.44	-	0.55	V
I _{CC}	supply current	V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 5.5 V	-	-	1.0	-	10	-	40	µA
C _I	input capacitance		-	1.5	10	-	10	-	10	pF

11. Dynamic characteristics

Table 8. Dynamic characteristics
GND = 0 V. For test circuit see [Figure 6](#).

Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
t_{pd}	propagation delay	A to Y; see Figure 5 [1]								
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$ [2]								
		$C_L = 15 \text{ pF}$	-	3.4	7.1	1.0	8.5	1.0	10.0	ns
		$C_L = 50 \text{ pF}$	-	4.9	10.6	1.0	12.0	1.0	13.5	ns
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$ [3]								
		$C_L = 15 \text{ pF}$	-	2.6	5.5	1.0	6.0	1.0	7.0	ns
C_{PD}	power dissipation capacitance	$C_L = 50 \text{ pF}$	-	3.6	7.0	1.0	8.0	1.0	9.0	ns
		per buffer; $V_I = \text{GND to } V_{CC}$ [4]	-	14	-	-	-	-	-	pF

[1] t_{pd} is the same as t_{PLH} and t_{PHL} .

[2] Typical values are measured at $V_{CC} = 3.3 \text{ V}$.

[3] Typical values are measured at $V_{CC} = 5.0 \text{ V}$.

[4] C_{PD} is used to determine the dynamic power dissipation P_D (μW).

$P_D = C_{PD} \times V_{CC}^2 \times f_i + \Sigma(C_L \times V_{CC}^2 \times f_o)$ where:

f_i = input frequency in MHz;

f_o = output frequency in MHz;

C_L = output load capacitance in pF;

V_{CC} = supply voltage in Volts.

12. Waveforms

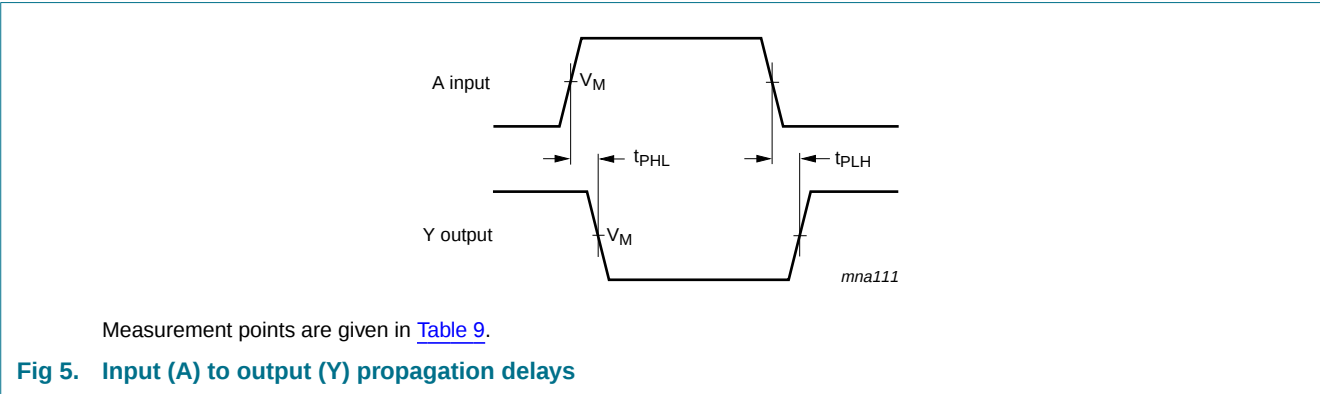


Table 9. Measurement point

Type	Input	Input	Output
	V_I	V_M	V_M
XC7SHU04	GND to V_{CC}	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$

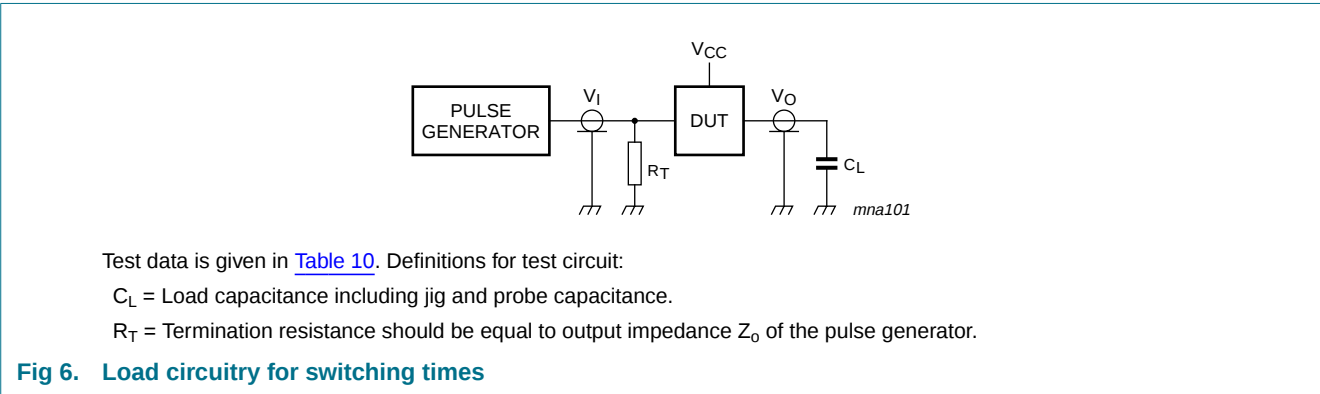
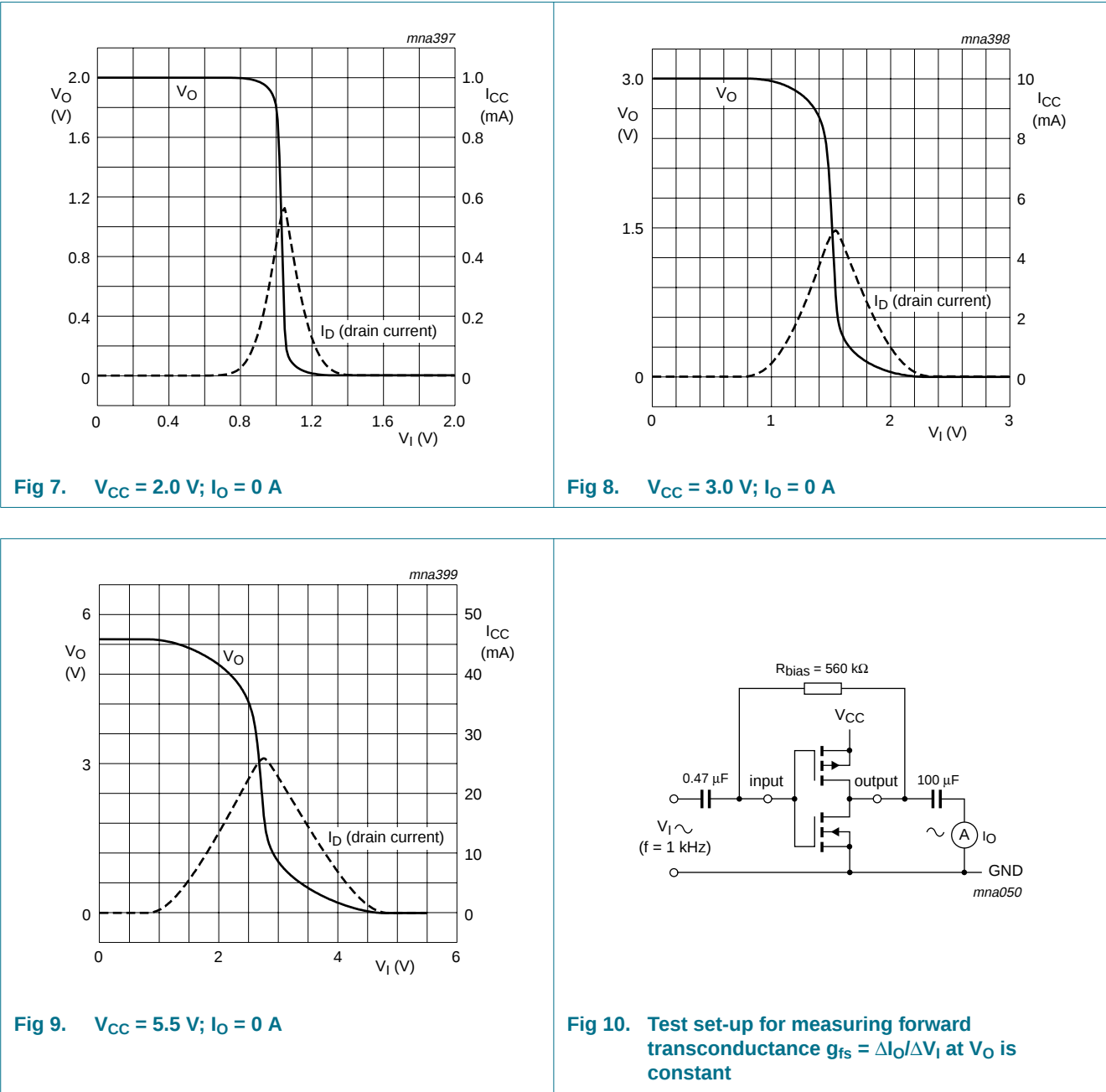


Table 10. Test data

Type	Input		Load	Test
	V_I	t_r, t_f	C_L	
XC7SHU04	V_{CC}	$\leq 3.0 \text{ ns}$	15 pF, 50 pF	t_{PLH}, t_{PHL}

13. Typical transfer characteristics



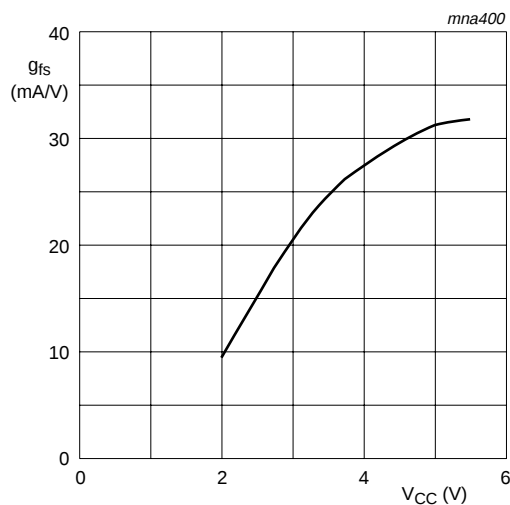


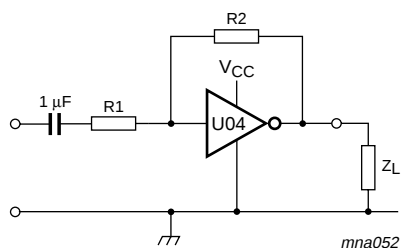
Fig 11. Typical forward transconductance g_{fs} as a function of the supply voltage at $T_{amb} = 25\text{ }^{\circ}\text{C}$

14. Application information

Some applications are:

- Linear amplifier (see [Figure 12](#))
- In crystal oscillator design (see [Figure 13](#))

Remark: All values given are typical unless otherwise specified.



Maximum $V_{O(p-p)} = V_{CC} - 1.5\text{ V}$ centered at $0.5 \times V_{CC}$.

$$G_v = -\frac{G_{ol}}{1 + \frac{R1}{R2}(1 + G_{ol})}$$

G_{ol} = open loop gain

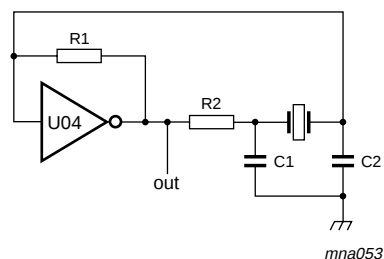
G_v = voltage gain

$R1 \geq 3\text{ k}\Omega$, $R2 \leq 1\text{ M}\Omega$

$Z_L > 10\text{ k}\Omega$; $G_{ol} = 20$ (typ.)

Typical unity gain bandwidth product is 5 MHz.

Fig 12. Used as a linear amplifier



$C1 = 47\text{ pF}$ (typ.)

$C2 = 22\text{ pF}$ (typ.)

$R1 = 1\text{ M}\Omega$ to $10\text{ M}\Omega$ (typ.)

$R2$ optimum value depends on the frequency and required stability against changes in V_{CC} or average minimum I_{CC} (I_{CC} is typically 2 mA at $V_{CC} = 3\text{ V}$ and $f = 1\text{ MHz}$).

Fig 13. Crystal oscillator configuration

Table 11. External components for resonator (f < 1 MHz)*All values given are typical and must be used as an initial set-up.*

Frequency	R1	R2	C1	C2
10 kHz to 15.9 kHz	22 M Ω	220 k Ω	56 pF	20 pF
16 kHz to 24.9 kHz	22 M Ω	220 k Ω	56 pF	10 pF
25 kHz to 54.9 kHz	22 M Ω	100 k Ω	56 pF	10 pF
55 kHz to 129.9 kHz	22 M Ω	100 k Ω	47 pF	5 pF
130 kHz to 199.9 kHz	22 M Ω	47 k Ω	47 pF	5 pF
200 kHz to 349.9 kHz	22 M Ω	47 k Ω	47 pF	5 pF
350 kHz to 600 kHz	22 M Ω	47 k Ω	47 pF	5 pF

Table 12. Optimum value for R2

Frequency	R2	Optimum for
3 kHz	2.0 k Ω	minimum required I _{CC}
	8.0 k Ω	minimum influence due to change in V _{CC}
6 kHz	1.0 k Ω	minimum required I _{CC}
	4.7 k Ω	minimum influence by V _{CC}
10 kHz	0.5 k Ω	minimum required I _{CC}
	2.0 k Ω	minimum influence by V _{CC}
14 kHz	0.5 k Ω	minimum required I _{CC}
	1.0 k Ω	minimum influence by V _{CC}
> 14 kHz	-	replace R2 by C3 with a typical value of 35 pF

15. Package outline

TSSOP5: plastic thin shrink small outline package; 5 leads; body width 1.25 mm

SOT353-1

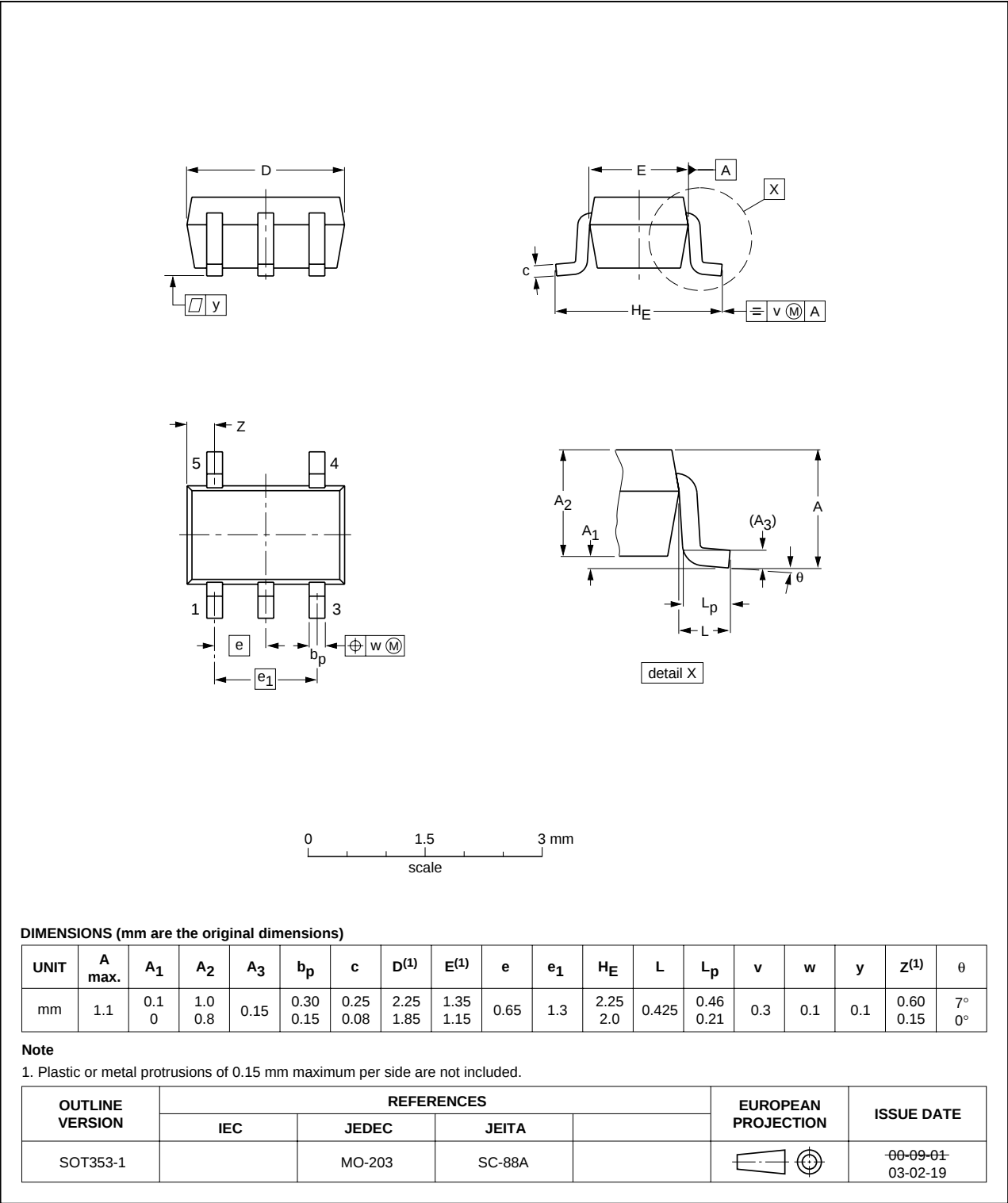


Fig 14. Package outline SOT353-1 (TSSOP5)

Plastic surface-mounted package; 5 leads

SOT753

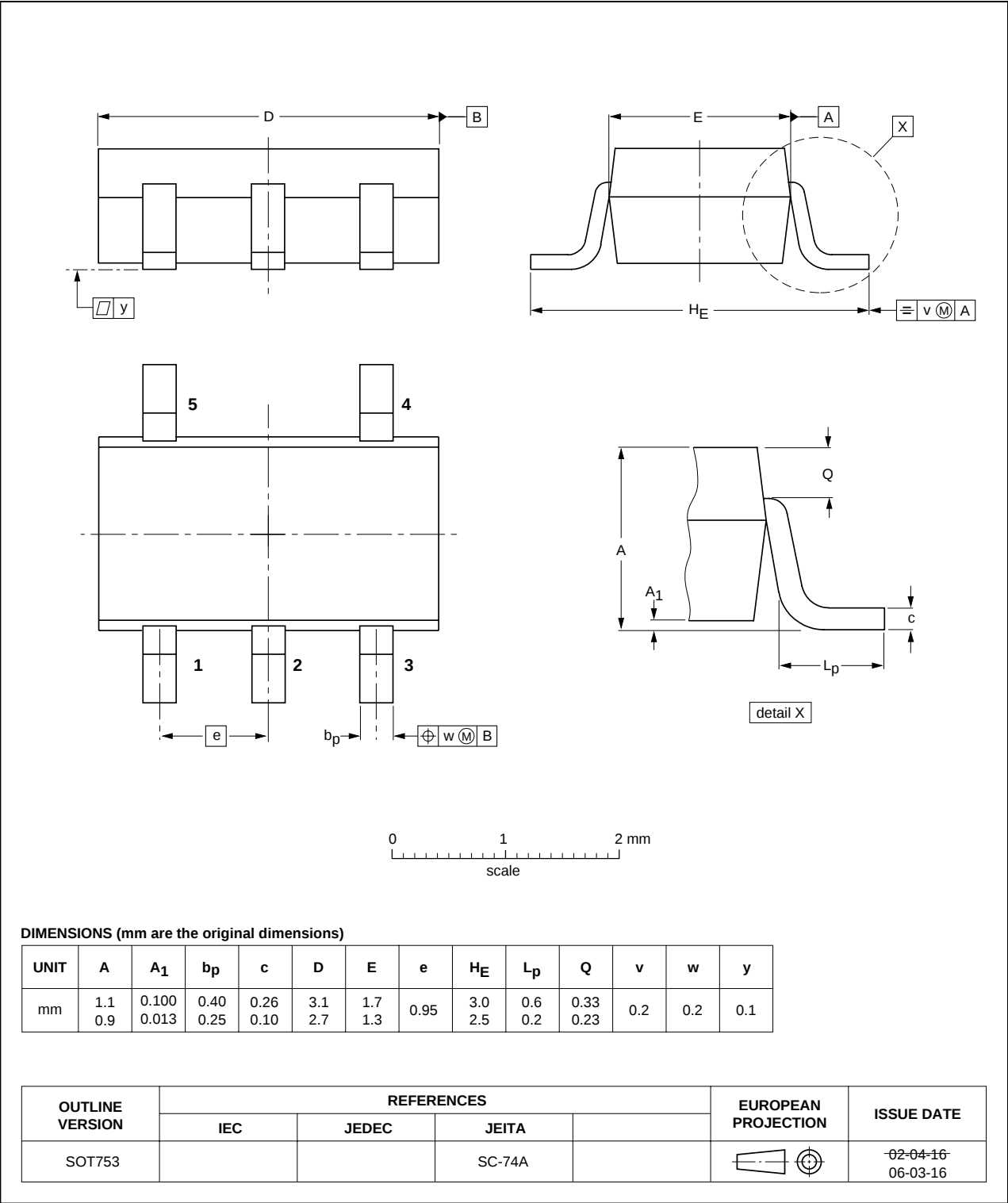


Fig 15. Package outline SOT753 (SC-74A)

16. Abbreviations

Table 13. Abbreviations

Acronym	Description
CDM	Charged Device Model
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model

17. Revision history

Table 14. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
XC7SHU04_1	20090907	Product data sheet	-	-

18. Legal information

18.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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[2] The term 'short data sheet' is explained in section "Definitions".

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